Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A magnetic random access memory array comprising:

a plurality of magnetic storage cells;

a plurality of global word lines;

a plurality of word line segments, each of the plurality of word line segments being coupled with at least one of the plurality of global word lines such that the plurality of word line segments is selectable, each of the plurality of word line segments being coupled to a first portion of the plurality of magnetic storage cells ~~{Stone, I replaced the "first portion" because otherwise the claim would read that each segment is coupled to all of the magnetic storage cells, which is not correct. Instead, each segment is coupled to some of the magnetic storage cells}~~;

a plurality of global bit lines;

a plurality of bit line segments, each of the plurality of bit line segments being coupled with at least one of the plurality of global bit lines such the plurality of bit line segments is selectable, each of the plurality of bit line segments residing in proximity to a second portion of the plurality of magnetic storage cells to write to the second portion of the plurality of magnetic storage cells~~{Stone, I put back the "second portion" for the same reason as above. Each bit line segment is only coupled to some of the magnetic storage cells in the memory, not all of them}~~; and

a plurality of selection devices, the plurality of bit line segments and the plurality of word line segments being coupled with and selectable using the plurality of selection devices.

2. (Original) The magnetic random access memory array of claim 1 wherein the plurality of global bit lines is substantially parallel to the plurality of global word lines.

3. (Currently Amended) The magnetic random access memory array of claim 1 further comprising:

at least one global word line return coupled with at least one of the plurality of global word lines through at least one selection device.

4. (Original) The magnetic random access memory array of claim 3 wherein the at least one global word line return further includes a plurality of global word line returns.

5. (Original) The magnetic random access memory array of claim 4 wherein each of the plurality of global word line returns corresponds to one of the plurality of global word lines.

6. (Currently Amended) The magnetic random access memory array of claim 1 further comprising:

at least one global bit line return coupled with at least one of the plurality of global bit lines through at least one of the plurality of selection devices.

7. (Original) The magnetic random access memory array of claim 6 wherein the at least one global bit line return further includes a plurality of global bit line returns.

8. (Original) The magnetic random access memory array of claim 7 wherein each of the plurality of global bit line returns corresponds to one of the plurality of global bit lines.

9. (Currently Amended) The magnetic random access memory array of claim 1 wherein at least a portion of the plurality of word line segments is magnetic.

10. (Currently Amended) The magnetic random access memory array of claim 1 wherein at least a portion of the plurality of bit line segments is magnetic.

11. (Original) The magnetic random access memory array of claim 1 wherein the plurality of global bit lines have a lower resistance than the plurality of bit line segments.

12. (Original) The magnetic random access memory array of claim 1 wherein the plurality of global word lines have a lower resistance than the plurality of word line segments.

13. (Original) The magnetic random access memory array of claim 12 wherein each of the plurality of global word line segments has a thickness and a width, the thickness being less than the width.

14. (Original) The magnetic random access memory array of claim 13 wherein the thickness is less than or equal to one fourth of the width.

15. (Original) The magnetic random access memory array of claim 1 wherein the plurality of global bit lines and the plurality of global word lines are both manufactured on a particular metal layer.

16. (Original) The magnetic random access memory array of claim 1 wherein the plurality of selection devices include a plurality of transistors or a plurality of diodes

17. (Original) The magnetic random access memory array of claim 1 wherein each of the plurality of magnetic storage cells includes a magnetic tunneling junction including a free layer, a barrier layer, and a pinned layer, the plurality of word line segments being magnetically coupled with the free layer in each of the first portion of the magnetic storage cells.

18. (Cancelled)

19. (Cancelled)

20. (Cancelled)

21. (Cancelled)

22. (Cancelled)

23. (Cancelled)

24. (Cancelled)

25. (Cancelled)

26. (Cancelled)

27. (Cancelled)

28. (Original) A method of providing a magnetic random access memory array comprising:

(a) providing a plurality of magnetic storage cells;

(b) providing a plurality of global word lines;

(c) providing a plurality of word line segments, each of the plurality of word line segments being coupled with at least one of the plurality of global word lines such that the plurality of word line segments is selectable, each of the plurality of word line segments being coupled to a first portion of the plurality of magnetic storage cells;

(d) providing a plurality of global bit lines;

(e) providing a plurality of bit line segments, each of the plurality of bit line segments being coupled with at least one of the plurality of global bit lines such the plurality of bit line segments is selectable, each of the plurality of bit line segments residing in proximity to a second portion of the plurality of magnetic storage cells to write to the second portion of the plurality of magnetic storage cells; and

(f) providing a plurality of selection devices, the plurality of bit line segments and the plurality of word line segments being coupled with and selectable using the plurality of selection devices.